



Product Datasheet Revision: April 2015



X=1300 μm Y=1500 μm

Features

RF frequency: 91 to 99 GHz

Conversion Loss: 11.5 dB, (typ.)

Singly balanced

 Functions as an up-converter or downconverter

♦ Die Size: < 2.0 sq. mm</p>

Performance Characteristics ($T_{OP} = 25^{\circ}C$)

Specification	Min	Тур	Max	Unit
RF frequency	91		99	GHz
LO frequency	91		99	GHz
IF frequency	DC		3	GHz
LO pow er		10		dBm
Conversion loss				
Upconverter				dB
Dow nconverter		11.5	12.5	dB
LO-RF isolation		TBD		dB
RF return loss		TBD		dB
IF return loss		TBD		dB

Applications

- Short Haul / High Capacity Links
- Wireless LANs
- Sensors
- Radar

Product Description

The MBH100 is a W-Band monolithic HEMT schottky diode, singly balanced mixer designed for use in commercial digital radios and wireless LANs. The design requires no external bias and can be used as an upconverter and as a downconverter. To ensure rugged and reliable operation, HEMT devices are fully passivated. Both bond pad and backside metallization are Ti/Au, which is compatible with conventional die attach, thermocompression, and thermosonic wire bonding assembly techniques.

Absolute Maximum Ratings (T_{op} = 25°C)

Parameter	Min	Max	Unit
Input LO Drive		16	dBm
Assy. Temperature		300	°C
(60 seconds)			

Note: The data contained in this document is for information only. Northrop Grumman reserves the right to change without notice the specifications, designs, prices or conditions of sale, as they apply to this product. The product represented by this datasheet is subject to U.S. Export Law as contained in the Export Administration Regulations (EAR).

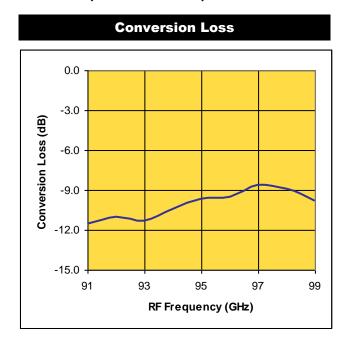
MBH100 91 – 99 GHz Mixer



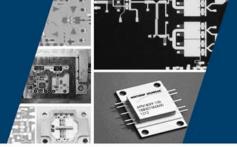


Product Datasheet Revision: April 2015

Measured Performance Characteristics (T_{OP} = 25°C) PLO= 10 dBm; PRF= -10 dBm; IF= 1 GHz



Note: The data contained in this document is for information only. Northrop Grumman reserves the right to change without notice the specifications, designs, prices or conditions of sale, as they apply to this product. The product represented by this datasheet is subject to U.S. Export Law as contained in the Export Administration Regulations (EAR).



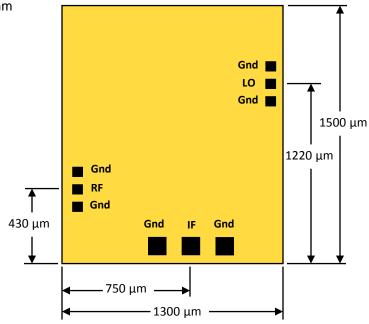


Product Datasheet Revision: April 2015

Die Size and Bond Pad Locations (Not to Scale)

X Dimension: 1300 ± 25 mm Y Dimension: 1500 ± 25 mm Bond Pad Dimensions:

IF: 101 x 101 mm \pm 0.5 mm RF & LO: 51 x 51 mm \pm 0.5 mm Chip Thickness = 101 \pm 5 μ m



Recommended Assembly Notes

- 1) Best performance obtained from use of <6 mil (long) by 1.5 by 0.5 mil ribbon on RF & LO ports.
- 2) Best performance obtained from use of <10 mil (long) by 3 by 0.5 mil ribbon on IF Port.

Note: The data contained in this document is for information only. Northrop Grumman reserves the right to change without notice the specifications, designs, prices or conditions of sale, as they apply to this product. The product represented by this datasheet is subject to U.S. Export Law as contained in the Export Administration Regulations (EAR).